A 0.115 $\mu$m\(^2\) 8F\(^2\) DRAM working cell with LPRD (Low_Prasitic_Resistance Device) and poly metal gate Technology for Gigabit DRAM

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Abstract

8F\(^2\) Stack DRAM cell 0.115 $\mu$m\(^2\) size has been successfully integrated employing selective epitaxial plug scheme for landing plug contacts and poly metal gates and MIM COB capacitors, of which cell working has been proven under easy function check mode. Cell transistor exhibits a sufficient saturation current ($I_{OP}$) of >40 $\mu$A with threshold voltage ($V_{tsat}$) of 1.0V.